

Martin Eickhoff

List of Publications by Year in descending order

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190
papers

7,449
citations

57758

44
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79
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195
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195
docs citations

195
times ranked

6782
citing authors

#	ARTICLE	IF	CITATIONS
1	Pyroelectric properties of Al(In)GaN/GaN hetero- and quantum well structures. Journal of Physics Condensed Matter, 2002, 14, 3399-3434.	1.8	864
2	Binary copper oxide semiconductors: From materials towards devices. Physica Status Solidi (B): Basic Research, 2012, 249, 1487-1509.	1.5	547
3	pH response of GaN surfaces and its application for pH-sensitive field-effect transistors. Applied Physics Letters, 2003, 83, 177-179.	3.3	264
4	Hydrogen response mechanism of Pt/GaN Schottky diodes. Applied Physics Letters, 2002, 80, 1222-1224.	3.3	197
5	Gas sensitive GaN/AlGaIn-heterostructures. Sensors and Actuators B: Chemical, 2002, 87, 425-430.	7.8	179
6	Playing with Polarity. Physica Status Solidi (B): Basic Research, 2001, 228, 505-512.	1.5	164
7	Polarity Assignment in ZnTe, GaAs, ZnO, and GaN-AlN Nanowires from Direct Dumbbell Analysis. Nano Letters, 2012, 12, 2579-2586.	9.1	161
8	GaN-based heterostructures for sensor applications. Diamond and Related Materials, 2002, 11, 886-891.	3.9	150
9	Direct biofunctionalization of semiconductors: A survey. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 3424-3437.	1.8	150
10	Al _x Ga _{1-x} N: A New Material System for Biosensors. Advanced Functional Materials, 2003, 13, 841-846.	14.9	146
11	Nucleation and growth of GaN nanorods on Si (111) surfaces by plasma-assisted molecular beam epitaxy - The influence of Si- and Mg-doping. Journal of Applied Physics, 2008, 104, .	2.5	136
12	Chemical functionalization of GaN and AlN surfaces. Applied Physics Letters, 2005, 87, 263901.	3.3	128
13	Electronics and sensors based on pyroelectric AlGaIn/GaN heterostructures - Part B: Sensor applications. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1908-1918.	0.8	124
14	Recording of cell action potentials with AlGaIn/GaN field-effect transistors. Applied Physics Letters, 2005, 86, 033901.	3.3	112
15	Influence of surface oxides on hydrogen-sensitive Pd:GaN Schottky diodes. Applied Physics Letters, 2003, 83, 773-775.	3.3	96
16	Optical properties of Si- and Mg-doped gallium nitride nanowires grown by plasma-assisted molecular beam epitaxy. Journal of Applied Physics, 2008, 104, .	2.5	93
17	Optical properties and structural characteristics of ZnMgO grown by plasma assisted molecular beam epitaxy. Journal of Applied Physics, 2009, 105, .	2.5	93
18	AlN/diamond heterojunction diodes. Applied Physics Letters, 2003, 82, 290-292.	3.3	92

#	ARTICLE	IF	CITATIONS
19	Silicon compatible materials for harsh environment sensors. <i>Sensors and Actuators A: Physical</i> , 1999, 74, 182-189.	4.1	86
20	Triple-twin domains in Mg doped GaN wurtzite nanowires: structural and electronic properties of this zinc-blende-like stacking. <i>Nanotechnology</i> , 2009, 20, 145704.	2.6	84
21	Group III-nitride-based gas sensors for combustion monitoring. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2002, 93, 207-214.	3.5	79
22	On the Low-Temperature Response of Semiconductor Gas Sensors. <i>Journal of Sensors</i> , 2009, 2009, 1-17.	1.1	66
23	A review of MBE grown 0D, 1D and 2D quantum structures in a nanowire. <i>Journal of Materials Chemistry C</i> , 2013, 1, 4300.	5.5	66
24	Electronics and sensors based on pyroelectric AlGaIn/GaN heterostructures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003, 0, 1878-1907.	0.8	65
25	Catalytic activity of enzymes immobilized on AlGaIn/GaN solution gate field-effect transistors. <i>Applied Physics Letters</i> , 2006, 89, 183901.	3.3	64
26	Optical properties of wurtzite/zinc-blende heterostructures in GaN nanowires. <i>Journal of Applied Physics</i> , 2011, 110, .	2.5	62
27	Bias-Enhanced Optical pH Response of Group III-Nitride Nanowires. <i>Nano Letters</i> , 2012, 12, 6180-6186.	9.1	60
28	GaN nanodiscs embedded in nanowires as optochemical transducers. <i>Nanotechnology</i> , 2011, 22, 275505.	2.6	59
29	Mn-rich clusters in GaN: Hexagonal or cubic symmetry?. <i>Applied Physics Letters</i> , 2005, 86, 131927.	3.3	58
30	Nanostructure and strain in InGaIn/GaN superlattices grown in GaN nanowires. <i>Nanotechnology</i> , 2013, 24, 435702.	2.6	58
31	A high temperature pressure sensor prepared by selective deposition of cubic silicon carbide on SOI substrates. <i>Sensors and Actuators A: Physical</i> , 1999, 74, 56-59.	4.1	54
32	UV Photosensing Characteristics of Nanowire-Based GaN/AlN Superlattices. <i>Nano Letters</i> , 2016, 16, 3260-3267.	9.1	53
33	Detection of oxidising gases using an optochemical sensor system based on GaN/InGaIn nanowires. <i>Sensors and Actuators B: Chemical</i> , 2014, 197, 87-94.	7.8	52
34	Optical properties of MgZnO alloys: Excitons and exciton-phonon complexes. <i>Journal of Applied Physics</i> , 2011, 110, .	2.5	50
35	Hydrosilylation of crystalline silicon (111) and hydrogenated amorphous silicon surfaces: A comparative x-ray photoelectron spectroscopy study. <i>Journal of Applied Physics</i> , 2003, 94, 2289-2294.	2.5	49
36	Vertical transport in group III-nitride heterostructures and application in AlN/GaN resonant tunneling diodes. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2004, 1, 2210-2227.	0.8	49

#	ARTICLE	IF	CITATIONS
37	<p>onfinement in GaN/Al</p> $\text{Ga} \times \text{N} \hat{=}$		

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73	Passivation layers for nanostructured photoanodes: ultra-thin oxides on InGaN nanowires. Journal of Materials Chemistry A, 2018, 6, 565-573.	10.3	26
74	A high temperature pressure sensor with $\hat{\Gamma}^2$ -SiC piezoresistors on SOI substrates. , 0, , .		25
75	A new SiC/HfB ₂ based low power gas sensor. Sensors and Actuators B: Chemical, 2001, 77, 111-115.	7.8	25
76	AlN/Diamond np-junctions. Diamond and Related Materials, 2003, 12, 1873-1876.	3.9	25
77	Ultrathin GaN/AlN/GaN solution-gate field effect transistor with enhanced resolution at low source-gate voltage. Sensors and Actuators B: Chemical, 2009, 142, 304-307.	7.8	25
78	Exciton confinement in homo- and heteroepitaxial ZnO/Zn _{1-x} Mg _x O quantum wells with $x \leq 0.1$. Journal of Applied Physics, 2011, 110, 093513.	2.5	25
79	Accurate determination of optical bandgap and lattice parameters of Zn _{1-x} Mg _x O epitaxial films (0 $\leq x \leq 0.3$) grown by plasma-assisted molecular beam epitaxy on a-plane sapphire. Journal of Applied Physics, 2013, 113, 233512.	2.5	25
80	Influence of crystal quality on the electronic properties of n-type 3C-SiC grown by low temperature low pressure chemical vapor deposition. Journal of Applied Physics, 2004, 95, 7908-7917.	2.5	24
81	Influence of crystal defects on the piezoresistive properties of 3C-SiC. Journal of Applied Physics, 2004, 96, 2878-2888.	2.5	23
82	Modulation spectroscopy of AlGaN/GaN heterostructures: The influence of electron-hole interaction. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 447-458.	1.8	23
83	Screening of the quantum-confined Stark effect in AlN/GaN nanowire superlattices by germanium doping. Applied Physics Letters, 2014, 104, .	3.3	23
84	Probing the Internal Electric Field in GaN/AlGaN Nanowire Heterostructures. Nano Letters, 2014, 14, 5118-5122.	9.1	23
85	Electrochemical properties of GaN nanowire electrodes— influence of doping and control by external bias. Nanotechnology, 2012, 23, 165701.	2.6	22
86	Effect of Water Vapor and Surface Morphology on the Low Temperature Response of Metal Oxide Semiconductor Gas Sensors. Materials, 2015, 8, 6570-6588.	2.9	22
87	Rare-Earth-Doped Y ₄ Al ₂ O ₉ Nanoparticles for Stable Light-Converting Phosphors. ACS Applied Nano Materials, 2020, 3, 699-710.	5.0	21
88	Dissociative Gas Sensing at Metal Oxide Surfaces. IEEE Sensors Journal, 2007, 7, 1675-1679.	4.7	20
89	Mg doping and its effect on the semipolar GaN(112 \hat{A} ²) growth kinetics. Applied Physics Letters, 2009, 95, 171908.	3.3	20
90	Rapid plasma etching of cubic SiC using NF ₃ /O ₂ gas mixtures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1997, 46, 160-163.	3.5	19

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91	Photoreflectance studies of (Al)Ga- and N-face AlGa _N /Ga _N heterostructures. Thin Solid Films, 2004, 450, 155-158.	1.8	19
92	Impact of silicon incorporation on the formation of structural defects in AlN. Journal of Applied Physics, 2006, 100, 113531.	2.5	19
93	Electrical transport properties of Ge-doped Ga _N nanowires. Nanotechnology, 2015, 26, 135704.	2.6	19
94	Photoluminescence Probing of Complex H ₂ O Adsorption on InGa _N /Ga _N Nanowires. Nano Letters, 2017, 17, 615-621.	9.1	19
95	Polytype transition of N-face Ga _N :Mg from wurtzite to zinc-blende. Journal of Applied Physics, 2004, 96, 3709-3715.	2.5	18
96	Doping-Induced Universal Conductance Fluctuations in Ga _N Nanowires. Nano Letters, 2015, 15, 7822-7828.	9.1	18
97	Observation of ion-induced changes in the channel current of high electron mobility AlGa _N /Ga _N transistors (HEMT). Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 93, 143-146.	3.5	17
98	Ga _N quantum dots as optical transducers for chemical sensors. Applied Physics Letters, 2009, 94, 113108.	3.3	17
99	Long-lived excitons in Ga _N /AlN nanowire heterostructures. Physical Review B, 2015, 91, .	3.2	17
100	Nitrogen incorporation in SnO ₂ thin films grown by chemical vapor deposition. Physica Status Solidi (B): Basic Research, 2016, 253, 1087-1092.	1.5	17
101	Oxidation Dependence on Defect Density in 3C-SiC Films. Journal of the Electrochemical Society, 2001, 148, G336.	2.9	16
102	Exciton quenching in Pt/Ga _N Schottky diodes with Ga- and N-face polarity. Applied Physics Letters, 2003, 82, 1712-1714.	3.3	16
103	Improved 3C-SiC Films Epitaxially Grown on Si by Flash Lamp Processing. Journal of the Electrochemical Society, 2004, 151, G136.	2.9	16
104	Electroreflectance spectroscopy of Pt ^δ -AlGa _N ^δ -Ga _N heterostructures exposed to gaseous hydrogen. Applied Physics Letters, 2006, 88, 024101.	3.3	16
105	Suppression of Si Cavities at the SiC/Si Interface during Epitaxial Growth of 3C-SiC on Silicon-on-Insulator. Journal of the Electrochemical Society, 2001, 148, G16.	2.9	15
106	Gas Sensing Interactions at Hydrogenated Diamond Surfaces. IEEE Sensors Journal, 2007, 7, 1349-1353.	4.7	15
107	Investigation of carrier dynamics in Zn _{1-x} Mg _x O by time-resolved photoluminescence. Journal of Luminescence, 2010, 130, 2256-2259.	3.1	15
108	Quantitative analysis of immobilized penicillinase using enzyme-modified AlGa _N /Ga _N field-effect transistors. Biosensors and Bioelectronics, 2015, 64, 605-610.	10.1	15

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109	Selective growth of high-quality 3C-SiC using a SiO ₂ sacrificial-layer technique. <i>Thin Solid Films</i> , 1999, 345, 197-199.	1.8	14
110	Electron injection-induced effects in Mn-doped GaN. <i>Journal of Applied Physics</i> , 2004, 96, 3556-3558.	2.5	14
111	Selective etching of AlInN/GaN heterostructures for MEMS technology. <i>Microelectronic Engineering</i> , 2007, 84, 1152-1156.	2.4	14
112	Gallium nitride electrodes for membrane-based electrochemical biosensors. <i>European Physical Journal E</i> , 2009, 30, 233-8.	1.6	14
113	Suppression of the quantum-confined Stark effect in polar nitride heterostructures. <i>Communications Physics</i> , 2018, 1, .	5.3	14
114	Controlled Laser-Thinning of MoS ₂ Nanolayers and Transformation to Amorphous MoO ₃ for 2D Monolayer Fabrication. <i>ACS Applied Nano Materials</i> , 2020, 3, 7490-7498.	5.0	14
115	High Temperature Piezoresistive $\hat{\text{I}}^2$ -SiC-on-SOI Pressure Sensor for Combustion Engines. <i>Materials Science Forum</i> , 1998, 264-268, 1101-1106.	0.3	13
116	Structural and interface properties of an AlN diamond ultraviolet light emitting diode. <i>Applied Physics Letters</i> , 2004, 85, 3699-3701.	3.3	13
117	Influence of thermal oxidation on the electronic properties of Pt Schottky contacts on GaN grown by molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2005, 86, 083507.	3.3	13
118	Contactless electroreflectance studies of free exciton binding energy in Zn _{1-x} Mg _x O epilayers. <i>Applied Physics Letters</i> , 2013, 103, 251908.	3.3	13
119	Shift of optical absorption edge in SnO ₂ films with high concentrations of nitrogen grown by chemical vapor deposition. <i>Journal of Applied Physics</i> , 2016, 119, .	2.5	13
120	Influence of the cluster constituents' reactivity on the desorption/ionization process induced by neutral SO ₂ clusters. <i>Journal of Chemical Physics</i> , 2017, 146, 134705.	3.0	13
121	Photoluminescence Detection of Surface Oxidation Processes on InGaN/GaN Nanowire Arrays. <i>ACS Sensors</i> , 2018, 3, 2254-2260.	7.8	13
122	SOL thickness dependence of residual strain in SOI material. <i>Electronics Letters</i> , 1999, 35, 1284.	1.0	12
123	A novel GaN-based multiparameter sensor system for biochemical analysis. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008, 5, 2361-2363.	0.8	12
124	ZnO/(ZnMg)O single quantum wells with high Mg content graded barriers. <i>Journal of Applied Physics</i> , 2012, 111, 113504.	2.5	12
125	Competitive adsorption of air constituents as observed on InGaN/GaN nano-optical probes. <i>Sensors and Actuators B: Chemical</i> , 2017, 250, 91-99.	7.8	12
126	Ion sensitive AlGaIn/GaN field-effect transistors with monolithically integrated wheatstone bridge for temperature- and drift compensation in enzymatic biosensors. <i>Sensors and Actuators B: Chemical</i> , 2018, 263, 20-26.	7.8	12

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127	Optical emission of GaN/AlN quantum-wires – the role of charge transfer from a nanowire template. <i>Nanoscale</i> , 2018, 10, 5591-5598.	5.6	12
128	Comparing Co-catalytic Effects of ZrO _x , SmO _x , and Pt on CO _x Methanation over Co-based Catalysts Prepared by Double Flame Spray Pyrolysis. <i>ChemCatChem</i> , 2021, 13, 2815-2831.	3.7	12
129	High quality $\hat{1}^2$ -SiC films obtained by low-temperature heteroepitaxy combined with a fast carbonization step. <i>Applied Physics A: Materials Science and Processing</i> , 1999, 68, 461-465.	2.3	11
130	Direct Observation of Mn Clusters in GaN by X-ray Scanning Microscopy. <i>Japanese Journal of Applied Physics</i> , 2004, 43, L695-L697.	1.5	11
131	Structural and electronic properties of GaN nanowires with embedded In _x Ga _{1-x} N nanodisks. <i>Journal of Applied Physics</i> , 2015, 118, 034301.	2.5	11
132	Plasma assisted molecular beam epitaxy of Cu ₂ O on MgO(001): Influence of copper flux on epitaxial orientation. <i>Journal of Crystal Growth</i> , 2016, 436, 87-91.	1.5	11
133	Anisotropic propagation of surface acoustic waves on nitride layers. <i>Superlattices and Microstructures</i> , 2004, 36, 815-823.	3.1	10
134	Optical properties of GaN-based nanowires containing a single Al _{0.14} Ga _{0.86} N/GaN quantum disc. <i>Nanotechnology</i> , 2013, 24, 125201.	2.6	10
135	Bias-Controlled Optical Transitions in GaN/AlN Nanowire Heterostructures. <i>ACS Nano</i> , 2017, 11, 8758-8767.	14.6	10
136	Synthesis of SnO ₂ Nanowires Using SnI ₂ as Precursor and Their Application as High-Performance Self-Powered Ultraviolet Photodetectors. <i>Physica Status Solidi (B): Basic Research</i> , 2018, 255, 1700426.	1.5	10
137	The beneficial role of flash lamp annealing on the epitaxial growth of the 3C-SiC on Si. <i>Applied Surface Science</i> , 2001, 184, 377-382.	6.1	9
138	Intra-excitonic relaxation dynamics in ZnO. <i>Applied Physics Letters</i> , 2011, 99, 231910.	3.3	9
139	Short-wavelength, mid- and far-infrared intersubband absorption in nonpolar GaN/Al(GaN) heterostructures. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 05FG05.	1.5	9
140	Hydrogen induced mobility enhancement in RF sputtered Cu ₂ O thin films. <i>Journal of Applied Physics</i> , 2016, 120, 185705.	2.5	9
141	Flexible Modulation of Electronic Band Structures of Wide Band Gap GaN Semiconductors Using Bioinspired, Nonbiological Helical Peptides. <i>Advanced Functional Materials</i> , 2018, 28, 1704034.	14.9	9
142	4D-STEM at interfaces to GaN: Centre-of-mass approach & NBED-disc detection. <i>Ultramicroscopy</i> , 2021, 228, 113321.	1.9	9
143	Stark shift of interband transitions in AlN $\hat{1}$ -GaN superlattices. <i>Applied Physics Letters</i> , 2007, 90, 241906.	3.3	8
144	Luminescent properties of ZnO and ZnMgO epitaxial layers under high hydrostatic pressure. <i>Journal of Alloys and Compounds</i> , 2016, 672, 125-130.	5.5	8

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145	Effects of the Fermi level energy on the adsorption of O ₂ to monolayer MoS ₂ . 2D Materials, 2018, 5, 045025.	4.4	8
146	Dynamic Extracellular Imaging of Biochemical Cell Activity Using InGaN/GaN Nanowire Arrays as Nanophotonic Probes. Advanced Functional Materials, 2018, 28, 1802503.	14.9	7
147	Fabrication of freestanding GaN microstructures using AlN sacrificial layers. Physica Status Solidi - Rapid Research Letters, 2007, 1, R10-R12.	2.4	6
148	Strain effects and phonon-plasmon coupled modes in Si-doped AlN. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 1183-1186.	1.8	6
149	p-type doping of semipolar GaN(11̄2) by plasma-assisted molecular-beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 1913-1915.	0.8	6
150	Effects of interface geometry on the thermoelectric properties of laterally microstructured ZnO-based thin films. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 119-124.	1.8	6
151	Radical formation at the gallium nitride nanowire-electrolyte interface by photoactivated charge transfer. Nanotechnology, 2013, 24, 325701.	2.6	6
152	Consistent description of mesoscopic transport: Case study of current-dependent magnetoconductance in single GaN:Ge nanowires. Physical Review B, 2019, 100, .	3.2	6
153	Influence of the silicon overlayer thickness of SOI unibond substrates on ¹² -SiC heteroepitaxy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 61-62, 567-570.	3.5	5
154	Electrochemical stabilization of crystalline silicon with aromatic self-assembled monolayers in aqueous electrolytes. Physica Status Solidi (B): Basic Research, 2005, 242, 2838-2845.	1.5	5
155	Electron spin resonance of Zn _{1-x} Mg _x O thin films grown by plasma-assisted molecular beam epitaxy. Applied Physics Letters, 2010, 97, 092102.	3.3	5
156	Probing carrier populations in ZnO quantum wells by screening of the internal electric fields. Physical Review B, 2013, 87, .	3.2	5
157	Integration of an opto-chemical detector based on group III-nitride nanowire heterostructures. Applied Optics, 2015, 54, 839.	1.8	5
158	In situ monitoring of myenteric neuron activity using acetylcholinesterase-modified AlGaIn/GaN solution-gate field-effect transistors. Biosensors and Bioelectronics, 2016, 77, 1048-1054.	10.1	5
159	Fully unstrained GaN on sacrificial AlN layers by nano-heteroepitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 2248-2251.	0.8	4
160	Analysis of polarization-dependent photorefectance studies for c-plane GaN films grown on a-plane sapphire. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 773-779.	1.8	4
161	Growth study of nonpolar Zn _{1-x} Mg _x O epitaxial films on a-plane bulk ZnO by plasma-assisted molecular beam epitaxy. Applied Physics Letters, 2012, 101, 122106.	3.3	4
162	III-nitride nanostructures for optical gas detection and pH sensing. Proceedings of SPIE, 2013, , .	0.8	4

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163	InGaN/GaN quantum dots as optical probes for the electric field at the GaN/electrolyte interface. Journal of Applied Physics, 2013, 114, 074313.	2.5	4
164	High Precision, Electrochemical Detection of Reversible Binding of Recombinant Proteins on Wide Bandgap GaN Electrodes Functionalized with Biomembrane Models. Advanced Functional Materials, 2014, 24, 4927-4934.	14.9	4
165	Self-assembly of ordered wurtzite/rock salt heterostructures – A new view on phase separation in $Mg_xZn_{1-x}O$. Journal of Applied Physics, 2015, 118, .	2.5	4
166	Evidence for nitrogen-related deep acceptor states in SnO ₂ grown by chemical vapor deposition. Journal of Applied Physics, 2017, 122, 205702.	2.5	4
167	Photoelectrochemical response of GaN, InGaN, and GaNP nanowire ensembles. Journal of Applied Physics, 2018, 123, 175703.	2.5	4
168	Optical Analysis of Oxygen Self-Diffusion in Ultrathin CeO ₂ Layers at Low Temperatures. Advanced Energy Materials, 2018, 8, 1802120.	19.5	4
169	Luminescence probing of surface adsorption processes using InGaN/GaN nanowire heterostructure arrays. , 2020, , 239-270.		4
170	Surface Microscopy of Atomic and Molecular Hydrogen from Field-Evaporating Semiconductors. Journal of Physical Chemistry C, 2021, 125, 17078-17087.	3.1	4
171	Micro-optical system as integration platform for III-N nanowire based opto-chemical detectors. Proceedings of SPIE, 2013, , .	0.8	3
172	Group III-Nitride Chemical Nanosensors with Optical Readout. Springer Series on Chemical Sensors and Biosensors, 2014, , 311-338.	0.5	3
173	Interfacial properties of self-assembled GaN nanowires on pre-processed Al ₂ O ₃ (0001) surfaces. Materials Science in Semiconductor Processing, 2016, 55, 46-50.	4.0	3
174	Transport mechanisms in SnO ₂ :N,H thin film grown by chemical vapor deposition. Physica Status Solidi (B): Basic Research, 2017, 254, 1700003.	1.5	3
175	Three dimensional reconstruction of InGaN nanodisks in GaN nanowires: Improvement of the nanowire sample preparation to avoid missing wedge effects. Journal of Crystal Growth, 2017, 475, 202-207.	1.5	3
176	Influence of the atom source operating parameters on the structural and optical properties of In _x Ga _{1-x} N nanowires grown by plasma-assisted molecular beam epitaxy. Journal of Applied Physics, 2018, 124, 165703.	2.5	3
177	Behavior of the $\hat{\mu}$ -Ga ₂ O ₃ :Sn Evaporation During Laser-Assisted Atom Probe Tomography. Microscopy and Microanalysis, 2021, 27, 687-695.	0.4	3
178	Time-resolved cathodoluminescence investigations of AlN:Ge/GaN nanowire structures. Nano Express, 2021, 2, 034001.	2.4	3
179	New High-Temperature Sensors for Innovative Engine Management. , 1998, , 223-230.		3
180	Novel Sensor Applications of group-III nitrides. Materials Research Society Symposia Proceedings, 2001, 693, 253.	0.1	2

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181	Phase transition by Mg doping of N-face polarity GaN. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2216-2219.	0.8	2
182	Study of the carrier transfer across the GaNP nanowire electrolyte interface by electron paramagnetic spin trapping. Applied Physics Letters, 2017, 110, 222101.	3.3	2
183	Temperature-dependent electric fields in GaN Schottky diodes studied by electroreflectance. Thin Solid Films, 2004, 450, 163-166.	1.8	1
184	Carrier dynamics in (ZnMg)O alloy materials. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1149-1152.	0.8	1
185	Optical manipulation of a multilevel nuclear spin in ZnO: Master equation and experiment. Physical Review B, 2016, 93, .	3.2	1
186	GaN Quantum Dots as Optical Transducers in Field Effect Chemical Sensors. , 2007, , .		0
187	GaN/AlN Axial Multi Quantum Well Nanowires for Optoelectronic Devices. , 2009, , .		0
188	Optical characterization of AlGaIn/GaN quantum disc structures in single nanowires. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2243-2245.	0.8	0
189	Chemically Sensitive Photoluminescence of InGaIn/GaN Nanowire Heterostructure Arrays. Proceedings (mdpi), 2019, 14, 43.	0.2	0
190	Detection of Hydrogen Dissolved in Liquid Media: A Review and Outlook. Physica Status Solidi (A) Applications and Materials Science, 2022, 219, .	1.8	0